

of an electronic or microelectronic component, whose layer thickness is at most 50 μm , wherein firstly --

On page 5, lines 13-14, replace the paragraph with:

-- The thickness of the insulating layer is preferably between 0.05 and 50 μm , particularly preferably between 0.1 and 20 μm .
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Remarks:

Reconsideration of the application is requested.

Claims 4-7 remain in the application.

In item 2 on page 2 of the above-identified Office action, the disclosure has been objected to because of the following informalities: The Examiner stated that on page 3, line 21 and on page 5, line 14, the term "FM" appears to be a typographical error, which should be recited as 50 μm .

The defect has been corrected.

In item 3 on page 2 of the Office action, claims 4-7 have been rejected as being obvious over Arbach et al. (5,021,129) in view of Angelopoulos et al. (6,136,513) and Bickford et al.